Renesas Electronics America Inc - R5F10ELCAFB#V0 Datasheet

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What is "Embedded - Microcontrollers"?

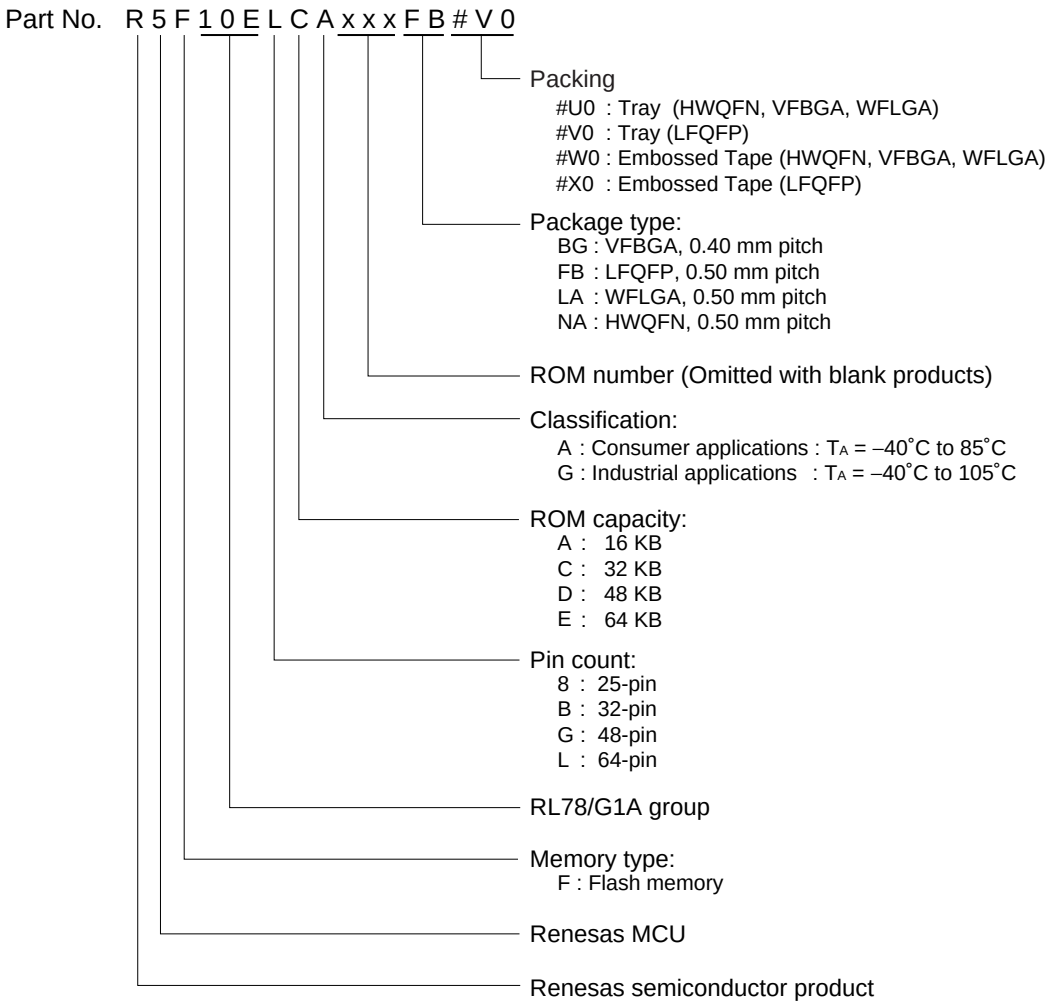
"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	RL78
Core Size	16-Bit
Speed	32MHz
Connectivity	CSI, I²C, LINbus, UART/USART
Peripherals	DMA, LVD, POR, PWM, WDT
Number of I/O	46
Program Memory Size	32KB (32K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	2K x 8
Voltage - Supply (Vcc/Vdd)	1.6V ~ 3.6V
Data Converters	A/D 28x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	64-LQFP
Supplier Device Package	64-LFQFP (10x10)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f10elcafb-v0

1.2 List of Part Numbers

Figure 1-1. Part Number, Memory Size, and Package of RL78/G1A



Caution The part number above is valid as of when this manual was issued. For the latest part number, see the web page of the target product on the Renesas Electronics website.

1.3.4 64-pin products

- 64-pin plastic LFQFP (10 × 10 mm, 0.5 mm pitch)

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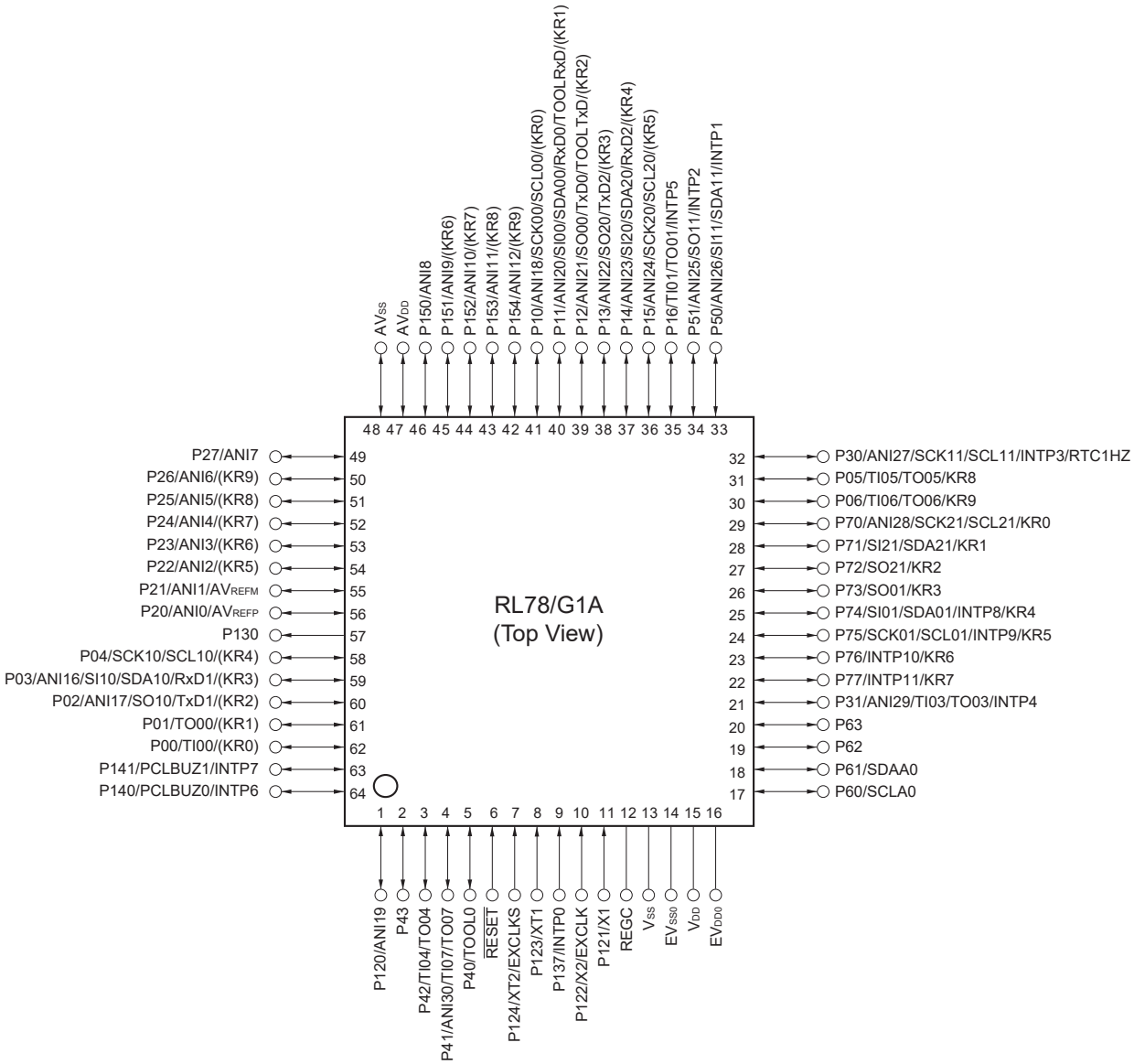


Cautions 1. Make EV_{SS0} pin the same potential as V_{SS} pin.

2. Make V_{DD} pin the potential that is higher than EV_{DD0} pin.

3. Connect the REGC pin to Vss via a capacitor (0.47 to 1 μF).

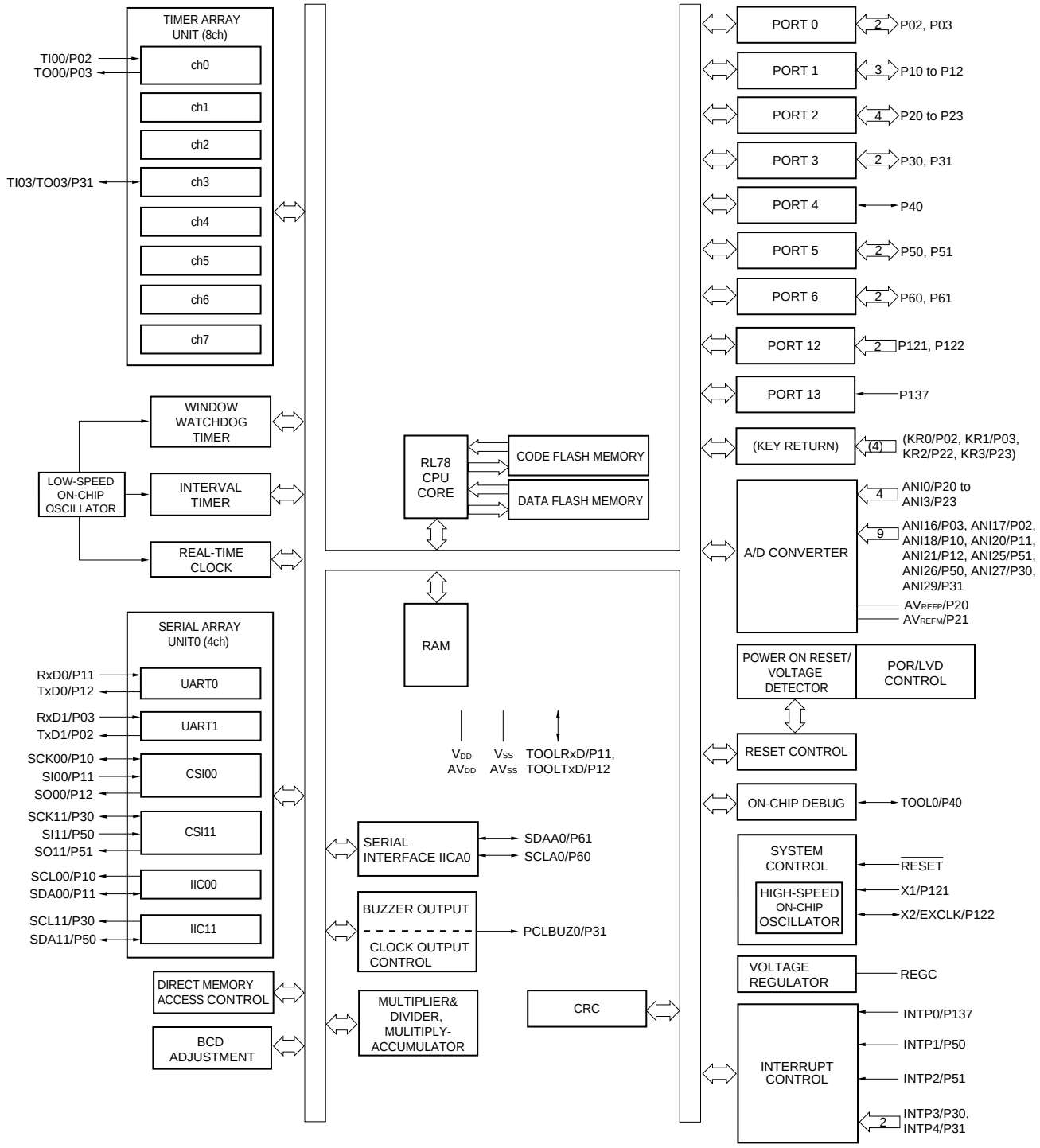
Remarks 1. For pin identification, see **1.4 Pin Identification.**

2. When using the microcontroller for an application where the noise generated inside the microcontroller must be reduced, it is recommended to supply separate powers to the V_{DD} and EV_{DD0} pins and connect the V_{SS} and EV_{SS}0pins to separate ground lines.

3. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR).

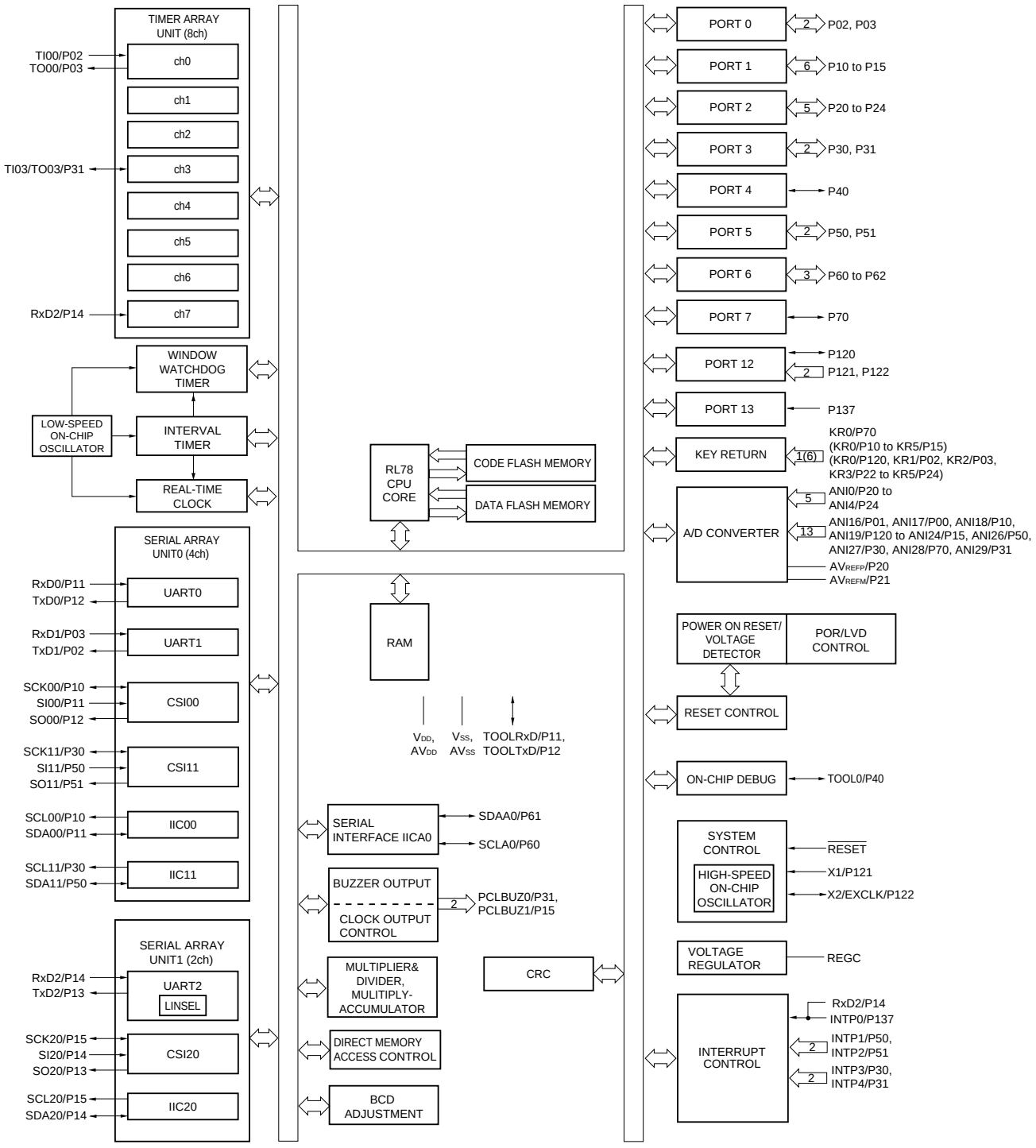
1.5 Block Diagram

1.5.1 25-pin products



Remark Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR).

<R> 1.5.2 32-pin products



Remark Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR).

(T_A = –40 to +85°C, 1.6 V ≤ AV_{DD} ≤ V_{DD} ≤ 3.6 V, 1.6 V ≤ EV_{DD0} ≤ V_{DD} ≤ 3.6 V, V_{SS} = EV_{SS0} = 0 V) **(3/5)**

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Input voltage, high	V_{IH1}	P00 to P06, P10 to P16, P30, P31, P40 to P43, P50, P51, P70 to P77, P120, P140, P141	Normal input buffer	0.8EV_{DD0}		EV_{DD0}	V
	V_{IH2}	P01, P03, P04, P10, P11, P13 to P16, P43	TTL input buffer 3.3 V ≤ EV_{DD0} ≤ 3.6 V	2.0		EV_{DD0}	V
			TTL input buffer 1.6 V ≤ EV_{DD0} < 3.3 V	1.5		EV_{DD0}	V
	V_{IH3}	P20 to P27, P150 to P154		0.7AV_{DD}		AV_{DD}	V
	V_{IH4}	P60 to P63		0.7EV_{DD0}		6.0	V
	V_{IH5}	P121 to P124, P137, EXCLK, EXCLKS, $\overline{\text{RESET}}$		0.8V_{DD}		V_{DD}	V
Input voltage, low	V_{IL1}	P00 to P06, P10 to P16, P30, P31, P40 to P43, P50, P51, P70 to P77, P120, P140, P141	Normal input buffer	0		0.2EV_{DD0}	V
	V_{IL2}	P01, P03, P04, P10, P11, P13 to P16, P43	TTL input buffer 3.3 V ≤ EV_{DD0} ≤ 3.6 V	0		0.5	V
			TTL input buffer 1.6 V ≤ EV_{DD0} < 3.3 V	0		0.32	V
	V_{IL3}	P20 to P27, P150 to P154		0		0.3AV_{DD}	V
	V_{IL4}	P60 to P63		0		0.3EV_{DD0}	V
	V_{IL5}	P121 to P124, P137, EXCLK, EXCLKS, $\overline{\text{RESET}}$		0		0.2V_{DD}	V

Caution The maximum value of V_{IH} of pins P00, P02 to P04, P10 to P15, P43, P50, P71, and P74 is EV_{DD0}, even in the N-ch open-drain mode.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

(T_A = –40 to +85°C, 1.6 V ≤ AV_{DD} ≤ V_{DD} ≤ 3.6 V, 1.6 V ≤ EV_{DD0} ≤ V_{DD} ≤ 3.6 V, V_{SS} = EV_{SS0} = 0 V) **(5/5)**

Items	Symbol	Conditions			MIN.	TYP.	MAX.	Unit
Input leakage current, high	I_{LIH1}	P00 to P06, P10 to P16, P30, P31, P40 to P43, P50, P51, P60 to P63, P70 to P77, P120, P140, P141	V_I = EV_{DD0}				1	μA
	I_{LIH2}	P137, $\overline{RESET}$	V_I = V_{DD}				1	μA
	I_{LIH3}	P121 to P124 (X1, X2, XT1, XT2, EXCLK, EXCLKS)	V_I = V_{DD}	In input port or external clock input			1	μA
				In resonator connection			10	μA
	I_{LIH4}	P20 to P27, P150 to P154	V_I = AV_{DD}				1	μA
Input leakage current, low	I_{LIL1}	P00 to P06, P10 to P16, P30, P31, P40 to P43, P50, P51, P60 to P67, P70 to P77, P120, P140, P141	V_I = EV_{SS0}				–1	μA
	I_{LIL2}	P137, $\overline{RESET}$	V_I = V_{SS}				–1	μA
	I_{LIL3}	P121 to P124 (X1, X2, XT1, XT2, EXCLK, EXCLKS)	V_I = V_{SS}	In input port or external clock input			–1	μA
				In resonator connection			–10	μA
	I_{LIL4}	P20 to P27, P150 to P154	V_I = AV_{SS}				–1	μA
On-chip pull-up resistance	R_U	P00 to P06, P10 to P16, P30, P31, P40 to P43, P50, P51, P70 to P77, P120, P140, P141	V_I = EV_{SS0}, In input port		10	20	100	kΩ

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

Note The following conditions are required for low-voltage interface when $EV_{DD0} < V_{DD}$.
1.8 V ≤ EV_{DD0} < 2.7 V : MIN. 125 ns
1.6 V ≤ EV_{DD0} < 1.8 V : MIN. 250 ns

Remark f_{MCK}: Timer array unit operation clock frequency
(Operation clock to be set by the CKS0n bit of timer clock select register 0 (TPS0) and timer mode register 0n (TMR0n). n: Channel number (n = 0 to 7))

Minimum Instruction Execution Time during Main System Clock Operation

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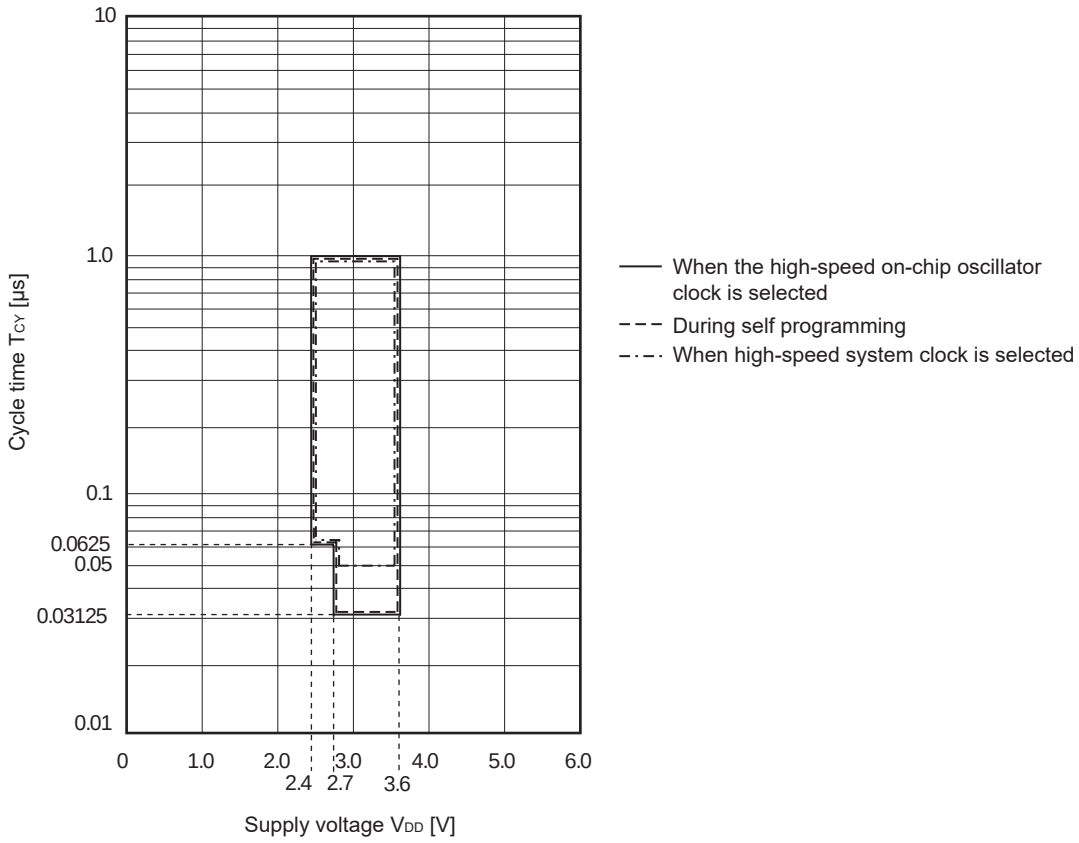
T_{CY} vs V_{DD} (HS (high-speed main) mode)



AC Timing Test Points

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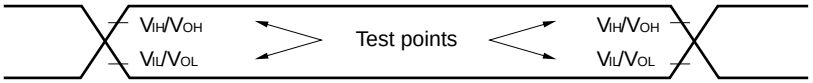
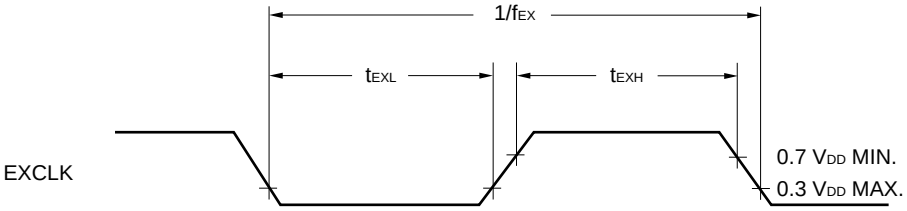
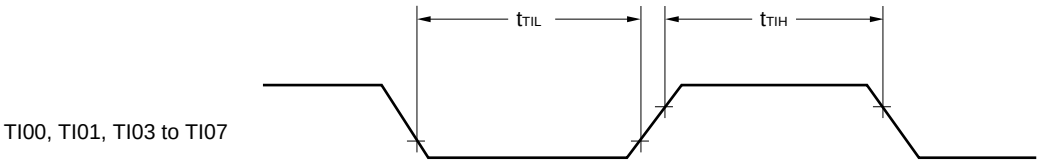
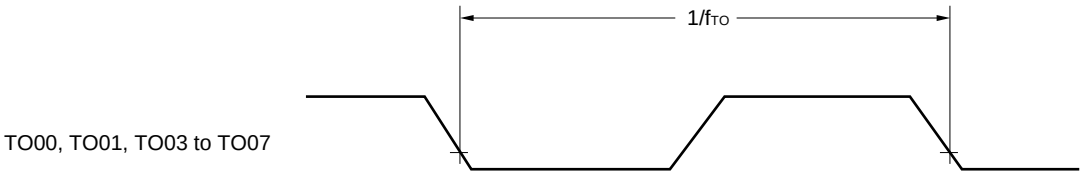


External System Clock Timing

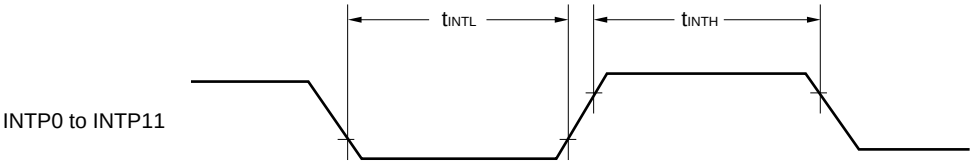


<R> TI/TO Timing

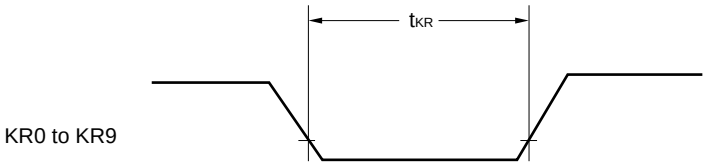




Interrupt Request Input Timing



Key Interrupt Input Timing



2.5 Peripheral Functions Characteristics

AC Timing Test Points

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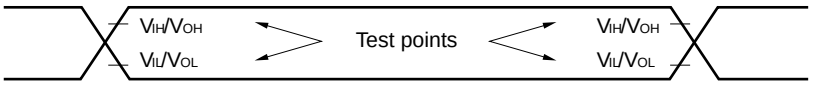


2.5.1 Serial array unit

(1) During communication at same potential (UART mode)

(T_A = –40 to +85°C, 1.6 V ≤ EV_{DD0} ≤ V_{DD} ≤ 3.6 V, V_{SS} = EV_{SS0} = 0 V)

Parameter	Symbol	Conditions	HS[Note 1]		LS[Note 2]		LV[Note 3]		Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Transfer rate[Note 4]		2.4 V ≤ EV_{DD} ≤ 3.6 V		f_{MCK}/6		f_{MCK}/6		f_{MCK}/6	bps
		Theoretical value of the maximum transfer rate f_{MCK} = f_{CLK}[Note 6]		5.3[Note 5]		1.3		0.6	Mbps
		1.8 V ≤ EV_{DD} ≤ 3.6 V		f_{MCK}/6		f_{MCK}/6		f_{MCK}/6	bps
		Theoretical value of the maximum transfer rate f_{MCK} = f_{CLK}[Note 6]		5.3[Note 5]		1.3		0.6	Mbps
		1.7 V ≤ EV_{DD} ≤ 3.6 V		f_{MCK}/6		f_{MCK}/6		f_{MCK}/6	bps
		Theoretical value of the maximum transfer rate f_{MCK} = f_{CLK}[Note 6]		5.3[Note 5]		1.3[Note 5]		0.6	Mbps
		1.6 V ≤ EV_{DD} ≤ 3.6 V		–		f_{MCK}/6		f_{MCK}/6	bps
		Theoretical value of the maximum transfer rate f_{MCK} = f_{CLK}[Note 6]		–		1.3[Note 5]		0.6	Mbps

Notes 1. HS is condition of HS (high-speed main) mode.

2. LS is condition of LS (low-speed main) mode.

3. LV is condition of LV (low-voltage main) mode.

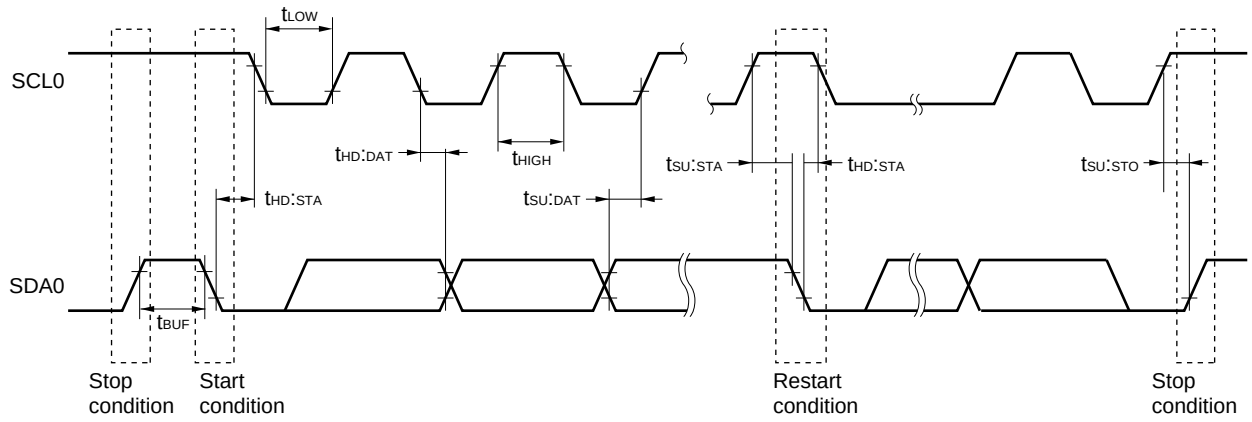
4. Transfer rate in the SNOOZE mode is 4800 bps.

5. The following conditions are required for low-voltage interface when EV_{DD0} < V_{DD}.
2.4 V ≤ EV_{DD0} < 2.7 V : MAX. 2.6 Mbps
1.8 V ≤ EV_{DD0} < 2.4 V : MAX. 1.3 Mbps
1.6 V ≤ EV_{DD0} < 1.8 V : MAX. 0.6 Mbps

6. f_{CLK} in each operating mode is as below.
HS (high-speed main) mode: f_{CLK} = 32 MHz
LS (low-speed main) mode: f_{CLK} = 8 MHz
LV (low-voltage main) mode: f_{CLK} = 4 MHz

Caution Select the normal input buffer for the RxDq pin and the normal output mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg).

IICA serial transfer timing



2.6 Analog Characteristics

2.6.1 A/D converter characteristics

Division of A/D Converter Characteristics

Reference voltag / Input channel	Reference voltage (+) = AV_{REFP} Reference voltage (–) = AV_{REFM}	Reference voltage (+) = AV_{DD} Reference voltage (–) = AV_{SS}	Reference voltage (+) = Internal refrence voltage Reference voltage (–) = AV_{SS}
High-accuracy channel; ANI0 to ANI12 (input buffer power supply: AV_{DD})	See **2.6.1 (1)** See **2.6.1 (2)**	See **2.6.1 (3)**	See **2.6.1 (6)**
Standard channel; ANI16 to ANI30 (input buffer power supply: V_{DD} or EV_{DD0})	See **2.6.1 (4)**	See **2.6.1 (5)**	
Temperature sensor, internal reference voltage output	See **2.6.1 (4)**	See **2.6.1 (5)**	–

<R> **(1) When reference voltage (+) = AV_{REFP}/ANI0 (ADREFP1 = 0, ADREFP0 = 1), reference voltage (–) = AV_{REFM}/ANI1 (ADREFM = 1), target for conversion: ANI2 to ANI12**

<R> **(T_A = –40 to +85°C, 2.4 V ≤ AV_{REFP} ≤ AV_{DD} ≤ V_{DD} ≤ 3.6 V, V_{SS} = 0 V, AV_{SS} = 0 V, Reference voltage (+) = AV_{REFP}, Reference voltage (–) = AV_{REFM} = 0 V, HALT mode)**

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Resolution	R_{ES}				12	bit
Overall error[Notes 1, 2, 3]	AINL	12-bit resolution		±1.7	±3.3	LSB
Conversion time	t_{CONV}	ADTYP = 0, 12-bit resolution	3.375			μs
Zero-scale error[Notes 1, 2, 3]	E_{ZS}	12-bit resolution		±1.3	±3.2	LSB
Full-scale error[Notes 1, 2, 3]	E_{FS}	12-bit resolution		±0.7	±2.9	LSB
Integral linearity error[Notes 1, 2, 3]	ILE	12-bit resolution		±1.0	±1.4	LSB
Differential linearity error[Notes 1, 2, 3]	DLE	12-bit resolution		±0.9	±1.2	LSB
Analog input voltage	V_{AIN}		0		AV_{REFP}	V

Notes 1. TYP. Value is the average value at AV_{DD} = AV_{REFP} = 3 V and T_A = 25°C. MAX. value is the average value ±3σ at normalized distribution.

2. These values are the results of characteristic evaluation and are not checked for shipment.

3. Excludes quantization error (±1/2 LSB).

Cautions 1. Route the wiring so that noise will not be superimposed on each power line and ground line, and insert a capacitor to suppress noise.
In addition, separate the reference voltage line of AV_{REFP} from the other power lines to keep it free from the influences of noise.

2. During A/D conversion, keep a pulse, such as a digital signal, that abruptly changes its level from being input to or output from the pins adjacent to the converter pins and P20 to P27 and P150 to P154.

<R> **(2) When reference voltage (+) = AV_{REFP}/ANI0 (ADREFP1 = 0, ADREFP0 = 1), reference voltage (–) = AV_{REFM}/ANI1 (ADREFM = 1), target for conversion: ANI2 to ANI12**

(T_A = –40 to +85°C, 1.6 V ≤ AV_{REFP} ≤ AV_{DD} ≤ V_{DD} ≤ 3.6 V, V_{SS} = 0 V, AV_{SS} = 0 V, Reference voltage (+) = AV_{REFP}, Reference voltage (–) = AV_{REFM} = 0 V)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Resolution	R_{ES}		2.4 V ≤ AV_{REFP} ≤ AV_{DD} ≤ 3.6 V	8		12	bit
			1.8 V ≤ AV_{REFP} ≤ AV_{DD} ≤ 3.6 V	8		10 Note 1	
			1.6 V ≤ AV_{REFP} ≤ AV_{DD} ≤ 3.6 V	8 Note 2			
Overall error Note 3	AINL	12-bit resolution	2.4 V ≤ AV_{REFP} ≤ AV_{DD} ≤ 3.6 V			±6.0	LSB
		10-bit resolution	1.8 V ≤ AV_{REFP} ≤ AV_{DD} ≤ 3.6 V			±5.0	
		8-bit resolution	1.6 V ≤ AV_{REFP} ≤ AV_{DD} ≤ 3.6 V			±2.5	
Conversion time	t_{CONV}	ADTYP = 0, 12-bit resolution	2.4 V ≤ AV_{REFP} ≤ AV_{DD} ≤ 3.6 V	3.375			μs
		ADTYP = 0, 10-bit resolution Note 1	1.8 V ≤ AV_{REFP} ≤ AV_{DD} ≤ 3.6 V	6.75			
		ADTYP = 0, 8-bit resolution Note 2	1.6 V ≤ AV_{REFP} ≤ AV_{DD} ≤ 3.6 V	13.5			
		ADTYP = 1, 8-bit resolution	2.4 V ≤ AV_{REFP} ≤ AV_{DD} ≤ 3.6 V	2.5625			
			1.8 V ≤ AV_{REFP} ≤ AV_{DD} ≤ 3.6 V	5.125			
			1.6 V ≤ AV_{REFP} ≤ AV_{DD} ≤ 3.6 V	10.25			
Zero-scale error Note 3	E_{ZS}	12-bit resolution	2.4 V ≤ AV_{REFP} ≤ AV_{DD} ≤ 3.6 V			±4.5	LSB
		10-bit resolution	1.8 V ≤ AV_{REFP} ≤ AV_{DD} ≤ 3.6 V			±4.5	
		8-bit resolution	1.6 V ≤ AV_{REFP} ≤ AV_{DD} ≤ 3.6 V			±2.0	
Full-scale error Note 3	E_{FS}	12-bit resolution	2.4 V ≤ AV_{REFP} ≤ AV_{DD} ≤ 3.6 V			±4.5	LSB
		10-bit resolution	1.8 V ≤ AV_{REFP} ≤ AV_{DD} ≤ 3.6 V			±4.5	
		8-bit resolution	1.6 V ≤ AV_{REFP} ≤ AV_{DD} ≤ 3.6 V			±2.0	
Integral linearity error Note 3	ILE	12-bit resolution	2.4 V ≤ AV_{REFP} ≤ AV_{DD} ≤ 3.6 V			±2.0	LSB
		10-bit resolution	1.8 V ≤ AV_{REFP} ≤ AV_{DD} ≤ 3.6 V			±1.5	
		8-bit resolution	1.6 V ≤ AV_{REFP} ≤ AV_{DD} ≤ 3.6 V			±1.0	
Differential linearity error Note 3	DLE	12-bit resolution	2.4 V ≤ AV_{REFP} ≤ AV_{DD} ≤ 3.6 V			±1.5	LSB
		10-bit resolution	1.8 V ≤ AV_{REFP} ≤ AV_{DD} ≤ 3.6 V			±1.5	
		8-bit resolution	1.6 V ≤ AV_{REFP} ≤ AV_{DD} ≤ 3.6 V			±1.0	
Analog input voltage	V_{AIN}			0		AV_{REFP}	V

Notes 1. Cannot be used for lower 2 bit of ADCR register

2. Cannot be used for lower 4 bit of ADCR register

3. Excludes quantization error (±1/2 LSB).

<R> **(3) When reference voltage (+) = AV_{DD} (ADREFP1 = 0, ADREFP0 = 0), reference voltage (–) = AV_{SS} (ADREFM = 0), target for conversion: ANI0 to ANI12**

(T_A = –40 to +85°C, 1.6 V ≤ AV_{DD} ≤ V_{DD} ≤ 3.6 V, V_{SS} = 0 V, AV_{SS} = 0 V, Reference voltage (+) = AV_{DD}, Reference voltage (–) = AV_{SS} = 0 V)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Resolution	R_{ES}		2.4 V ≤ AV_{DD} ≤ 3.6 V	8		12	bit
			1.8 V ≤ AV_{DD} ≤ 3.6 V	8		10 Note 1	
			1.6 V ≤ AV_{DD} ≤ 3.6 V	8 Note 2			
Overall error Note 3	AINL	12-bit resolution	2.4 V ≤ AV_{DD} ≤ 3.6 V			±7.5	LSB
		10-bit resolution	1.8 V ≤ AV_{DD} ≤ 3.6 V			±5.5	
		8-bit resolution	1.6 V ≤ AV_{DD} ≤ 3.6 V			±3.0	
Conversion time	t_{CONV}	ADTYP = 0, 12-bit resolution	2.4 V ≤ AV_{DD} ≤ 3.6 V	3.375			μs
		ADTYP = 0, 10-bit resolution Note 1	1.8 V ≤ AV_{DD} ≤ 3.6 V	6.75			
		ADTYP = 0, 8-bit resolution Note 2	1.6 V ≤ AV_{DD} ≤ 3.6 V	13.5			
		ADTYP = 1, 8-bit resolution	2.4 V ≤ AV_{DD} ≤ 3.6 V	2.5625			
			1.8 V ≤ AV_{DD} ≤ 3.6 V	5.125			
			1.6 V ≤ AV_{DD} ≤ 3.6 V	10.25			
Zero-scale error Note 3	E_{ZS}	12-bit resolution	2.4 V ≤ AV_{DD} ≤ 3.6 V			±6.0	LSB
		10-bit resolution	1.8 V ≤ AV_{DD} ≤ 3.6 V			±5.0	
		8-bit resolution	1.6 V ≤ AV_{DD} ≤ 3.6 V			±2.5	
Full-scale error Note 3	E_{FS}	12-bit resolution	2.4 V ≤ AV_{DD} ≤ 3.6 V			±6.0	LSB
		10-bit resolution	1.8 V ≤ AV_{DD} ≤ 3.6 V			±5.0	
		8-bit resolution	1.6 V ≤ AV_{DD} ≤ 3.6 V			±2.5	
Integral linearity error Note 3	ILE	12-bit resolution	2.4 V ≤ AV_{DD} ≤ 3.6 V			±3.0	LSB
		10-bit resolution	1.8 V ≤ AV_{DD} ≤ 3.6 V			±2.0	
		8-bit resolution	1.6 V ≤ AV_{DD} ≤ 3.6 V			±1.5	
Differential linearity error Note 3	DLE	12-bit resolution	2.4 V ≤ AV_{DD} ≤ 3.6 V			±2.0	LSB
		10-bit resolution	1.8 V ≤ AV_{DD} ≤ 3.6 V			±2.0	
		8-bit resolution	1.6 V ≤ AV_{DD} ≤ 3.6 V			±1.5	
<R> Analog input voltage	V_{AIN}			0		AV_{DD}	V

Notes 1. Cannot be used for lower 2 bit of ADCR register

2. Cannot be used for lower 4 bit of ADCR register

3. Excludes quantization error (±1/2 LSB).

<R> **(5) When reference voltage (+) = AV_{DD} (ADREFP1 = 0, ADREFP0 = 0), reference voltage (–) = AV_{SS} (ADREFM = 0), target for conversion: ANI16 to ANI30, interanal reference voltage, temperature sensor output voltage**

(T_A = –40 to +85°C, 1.6 V ≤ EV_{DD0} ≤ V_{DD0} ≤ 3.6 V, 1.6 V ≤ AV_{DD} ≤ V_{DD} ≤ 3.6 V, V_{SS} = EV_{SS0} = 0 V, AV_{SS} = 0 V, Reference voltage (+) = AV_{DD}, Reference voltage (–) = AV_{SS} = 0 V)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Resolution	R_{ES}		2.4 V ≤ AV_{DD} ≤ 3.6 V	8		12	bit
			1.8 V ≤ AV_{DD} ≤ 3.6 V	8		10 Note 1	
			1.6 V ≤ AV_{DD} ≤ 3.6 V	8 Note 2			
Overall error Note 3	AINL	12-bit resolution	2.4 V ≤ AV_{DD} ≤ 3.6 V			±8.5	LSB
		10-bit resolution	1.8 V ≤ AV_{DD} ≤ 3.6 V			±6.0	
		8-bit resolution	1.6 V ≤ AV_{DD} ≤ 3.6 V			±3.5	
Conversion time	t_{CONV}	ADTYP = 0, 12-bit resolution	2.4 V ≤ AV_{DD} ≤ 3.6 V	4.125			μs
		ADTYP = 0, 10-bit resolution Note 1	1.8 V ≤ AV_{DD} ≤ 3.6 V	9.5			
		ADTYP = 0, 8-bit resolution Note 2	1.6 V ≤ AV_{DD} ≤ 3.6 V	57.5			
		ADTYP = 1, 8-bit resolution	2.4 V ≤ AV_{DD} ≤ 3.6 V	3.3125			μs
			1.8 V ≤ AV_{DD} ≤ 3.6 V	7.875			
			1.6 V ≤ AV_{DD} ≤ 3.6 V	54.25			
Zero-scale error Note 3	E_{ZS}	12-bit resolution	2.4 V ≤ AV_{DD} ≤ 3.6 V			±8.0	LSB
		10-bit resolution	1.8 V ≤ AV_{DD} ≤ 3.6 V			±5.5	
		8-bit resolution	1.6 V ≤ AV_{DD} ≤ 3.6 V			±3.0	
Full-scale error Note 3	E_{FS}	12-bit resolution	2.4 V ≤ AV_{DD} ≤ 3.6 V			±8.0	LSB
		10-bit resolution	1.8 V ≤ AV_{DD} ≤ 3.6 V			±5.5	
		8-bit resolution	1.6 V ≤ AV_{DD} ≤ 3.6 V			±3.0	
Integral linearity error Note 3	ILE	12-bit resolution	2.4 V ≤ AV_{DD} ≤ 3.6 V			±3.5	LSB
		10-bit resolution	1.8 V ≤ AV_{DD} ≤ 3.6 V			±2.5	
		8-bit resolution	1.6 V ≤ AV_{DD} ≤ 3.6 V			±1.5	
Differential linearity error Note 3	DLE	12-bit resolution	2.4 V ≤ AV_{DD} ≤ 3.6 V			±2.5	LSB
		10-bit resolution	1.8 V ≤ AV_{DD} ≤ 3.6 V			±2.5	
		8-bit resolution	1.6 V ≤ AV_{DD} ≤ 3.6 V			±2.0	
Analog input voltage	V_{AIN}			0		AV_{DD} and EV_{DD0}	V
		Interanal reference voltage (2.4 V ≤ V_{DD} ≤ 3.6 V, HS (high-speed main) mode)		V_{BGR} Note 4			V
		Temperature sensor output voltage (2.4 V ≤ V_{DD} ≤ 3.6 V, HS (high-speed main) mode)		V_{TMPS25} Note 4			V

Notes 1. Cannot be used for lower 2 bit of ADCR register

2. Cannot be used for lower 4 bit of ADCR register

3. Excludes quantization error (±1/2 LSB).

4. See **2.6.2 Temperature sensor, internal reference voltage output characteristics**.

2.6.4 LVD circuit characteristics

LVD Detection Voltage of Reset Mode and Interrupt Mode

(T_A = –40 to +85°C, $V_{PDR} \le V_{DD} \le 3.6$ V, V_{SS} = 0 V)

Parameter		Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Detection voltage	Supply voltage level	V_{LVD2}	Power supply rise time	3.07	3.13	3.19	V
			Power supply fall time	3.00	3.06	3.12	V
		V_{LVD3}	Power supply rise time	2.96	3.02	3.08	V
			Power supply fall time	2.90	2.96	3.02	V
		V_{LVD4}	Power supply rise time	2.86	2.92	2.97	V
			Power supply fall time	2.80	2.86	2.91	V
		V_{LVD5}	Power supply rise time	2.76	2.81	2.87	V
			Power supply fall time	2.70	2.75	2.81	V
		V_{LVD6}	Power supply rise time	2.66	2.71	2.76	V
			Power supply fall time	2.60	2.65	2.70	V
		V_{LVD7}	Power supply rise time	2.56	2.61	2.66	V
			Power supply fall time	2.50	2.55	2.60	V
		V_{LVD8}	Power supply rise time	2.45	2.50	2.55	V
			Power supply fall time	2.40	2.45	2.50	V
		V_{LVD9}	Power supply rise time	2.05	2.09	2.13	V
			Power supply fall time	2.00	2.04	2.08	V
		V_{LVD10}	Power supply rise time	1.94	1.98	2.02	V
			Power supply fall time	1.90	1.94	1.98	V
		V_{LVD11}	Power supply rise time	1.84	1.88	1.91	V
			Power supply fall time	1.80	1.84	1.87	V
		V_{LVD12}	Power supply rise time	1.74	1.77	1.81	V
			Power supply fall time	1.70	1.73	1.77	V
		V_{LVD13}	Power supply rise time	1.64	1.67	1.70	V
			Power supply fall time	1.60	1.63	1.66	V
Minimum pulse width		t_{LW}		300			μs
Detection delay time						300	μs

Caution Set the detection voltage (V_{LVD}) to be within the operating voltage range. The operating voltage range depends on the setting of the user option byte (000C2H/010C2H). The following shows the operating voltage range.

HS (high-speed main) mode: V_{DD} = 2.7 to 3.6 V@1 MHz to 32 MHz

V_{DD} = 2.4 to 3.6 V@1 MHz to 16 MHz

LS (low-speed main) mode: V_{DD} = 1.8 to 3.6 V@1 MHz to 8 MHz

LV (low-voltage main) mode: V_{DD} = 1.6 to 3.6 V@1 MHz to 4 MHz

Notes 1. Total current flowing into V_{DD} and EV_{DD0}, including the input leakage current flowing when the level of the input pin is fixed to V_{DD}, EV_{DD0} or V_{SS}, EV_{SS0}. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, on-chip pull-up/pull-down resistors, and data flash rewriting.

2. When high-speed on-chip oscillator and subsystem clock are stopped.

3. When high-speed system clock and subsystem clock are stopped.

4. When high-speed on-chip oscillator and high-speed system clock are stopped. When setting ultra-low power consumption oscillation (AMPHS1 = 1). Not including the current flowing into the RTC, 12-bit interval timer and watchdog timer

5. Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.

HS (high-speed main) mode: V_{DD} = 2.7 V to 3.6 V@1 MHz to 32 MHz
V_{DD} = 2.4 V to 3.6 V@1 MHz to 16 MHz

Remarks 1. f_{MX}: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)

2. f_{IH}: High-speed on-chip oscillator clock frequency

3. f_{SUB}: Subsystem clock frequency (XT1 clock oscillation frequency)

4. Except subsystem clock operation, temperature condition of the TYP. value is T_A = 25°C

(T_A = –40 to +105°C, 2.4 V ≤ EV_{DD0} ≤ V_{DD} ≤ 3.6 V, V_{SS} = EV_{SS0} = 0 V) **(3/3)**

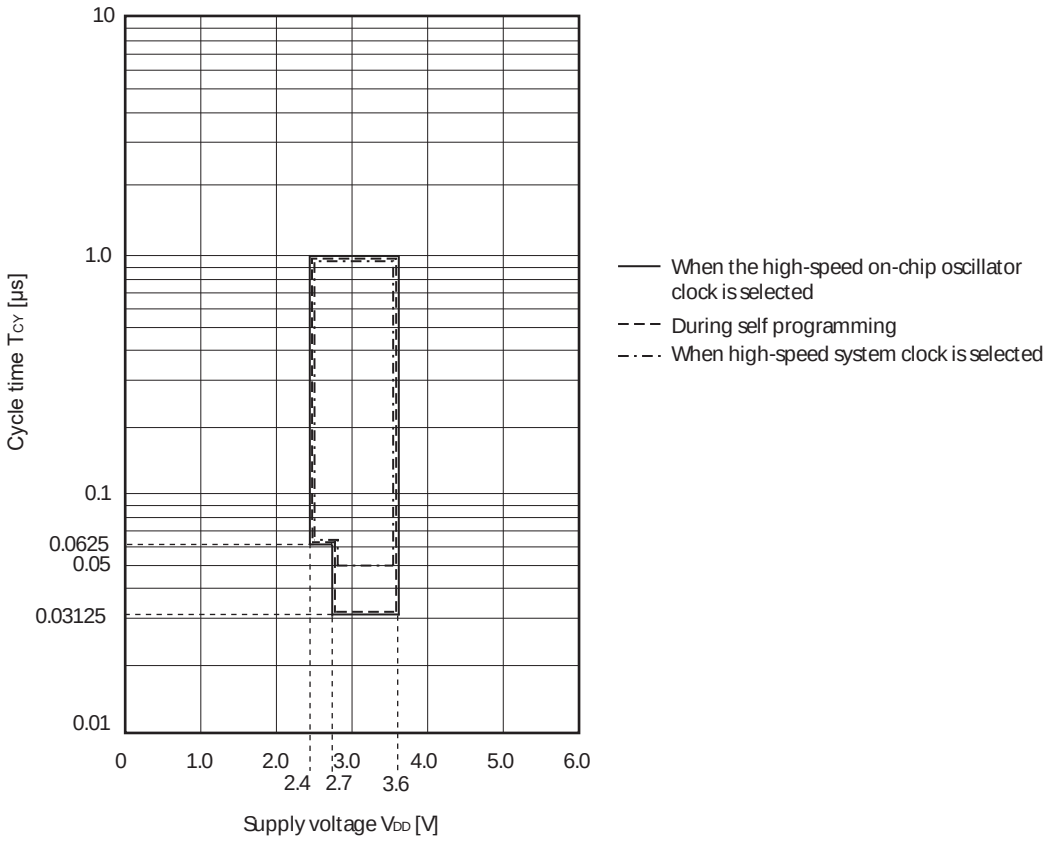
Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Low-speed on-chip oscillator operating current	I_{FIL} Note 1				0.20		μA
RTC operating current	I_{RTC} Notes 1, 2, 3				0.02		μA
12-bit interval timer operating current	I_{IT} Notes 1, 2, 4				0.02		μA
Watchdog timer operating current	I_{WDT} Notes 1, 2, 5	f_{IL} = 15 kHz			0.22		μA
A/D converter operating current	I_{ADC} Notes 6, 7	AV_{DD} = 3.0 V, When conversion at maximum speed			420	720	μA
$AV_{REF(+)}$ current	I_{AVREF} Note 8	AV_{DD} = 3.0 V, ADREFP1 = 0, ADREFP0 = 0 Note 7			14.0	25.0	μA
		AV_{REFP} = 3.0 V, ADREFP1 = 0, ADREFP0 = 1 Note 10			14.0	25.0	μA
		ADREFP1 = 1, ADREFP0 = 0 Note 1			14.0	25.0	μA
A/D converter reference voltage current	I_{ADREF} Notes 1, 9	V_{DD} = 3.0 V			75.0		μA
Temperature sensor operating current	I_{TMPS} Note 1	V_{DD} = 3.0 V			75.0		μA
LVD operating current	I_{LVD} Notes 1, 11				0.08		μA
BGO operating current	I_{BGO} Notes 1, 12				2.5	12.2	mA
Self-programming operating current	I_{FSP} Notes 1, 13				2.5	12.2	mA
SNOOZE operating current	I_{SNOZ}	A/D converter operation (AV_{DD} = 3.0 V)	The mode is performed Notes 1, 14		0.50	1.10	mA
			During A/D conversion Note 1		0.60	1.34	mA
			During A/D conversion Note 7		420	720	μA
		CSI/UART operation Note 1			0.70	1.54	mA

(**Notes** and **Remarks** are listed on the next page.)

Minimum Instruction Execution Time during Main System Clock Operation

<R>

T_{CY} vs V_{DD} (HS (high-speed main) mode)



(5) Communication at different potential (1.8 V, 2.5 V) (UART mode) (dedicated baud rate generator output) (1/2)

(T_A = –40 to +105°C, 2.4 V ≤ EV_{DD0} ≤ V_{DD} ≤ 3.6 V, V_{SS} = EV_{SS0} = 0 V)

Parameter	Symbol	Conditions			MIN.	TYP.	MAX.	Unit
Transfer rate[Note 1]		Reception	2.7 V ≤ EV_{DD0} ≤ 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V				f_{MCK}/12	bps
				Theoretical value of the maximum transfer rate f_{CLK} = 32 MHz, f_{MCK} = f_{CLK}			2.6	Mbps
			2.4 V ≤ EV_{DD0} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V				f_{MCK}/12	bps
				Theoretical value of the maximum transfer rate f_{CLK} = 32 MHz, f_{MCK} = f_{CLK}			2.6[Note 2]	Mbps

Notes 1. Transfer rate in the SNOOZE mode is 4800 bps.

2. The following conditions are required for low-voltage interface when EV_{DD0} < V_{DD}.
2.4 V ≤ EV_{DD0} < 2.7 V : MAX. 1.3 Mbps

Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (V_{DD} tolerance (When 25- to 48-pin products)/EV_{DD} tolerance (When 64-pin products)) mode for the TxDq pin by using <R> **port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.**

Remarks 1. V_b[V]: Communication line voltage

2. q: UART number (q = 0 to 2), g: PIM and POM number (g = 0, 1)

3. f_{MCK}: Serial array unit operation clock frequency
(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00 to 03, 10, 11)

NOTES FOR CMOS DEVICES

(1) VOLTAGE APPLICATION WAVEFORM AT INPUT PIN: Waveform distortion due to input noise or a reflected wave may cause malfunction. If the input of the CMOS device stays in the area between VIL (MAX) and VIH (MIN) due to noise, etc., the device may malfunction. Take care to prevent chattering noise from entering the device when the input level is fixed, and also in the transition period when the input level passes through the area between VIL (MAX) and VIH (MIN).

(2) HANDLING OF UNUSED INPUT PINS: Unconnected CMOS device inputs can be cause of malfunction. If an input pin is unconnected, it is possible that an internal input level may be generated due to noise, etc., causing malfunction. CMOS devices behave differently than Bipolar or NMOS devices. Input levels of CMOS devices must be fixed high or low by using pull-up or pull-down circuitry. Each unused pin should be connected to VDD or GND via a resistor if there is a possibility that it will be an output pin. All handling related to unused pins must be judged separately for each device and according to related specifications governing the device.

(3) PRECAUTION AGAINST ESD: A strong electric field, when exposed to a MOS device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop generation of static electricity as much as possible, and quickly dissipate it when it has occurred. Environmental control must be adequate. When it is dry, a humidifier should be used. It is recommended to avoid using insulators that easily build up static electricity. Semiconductor devices must be stored and transported in an anti-static container, static shielding bag or conductive material. All test and measurement tools including work benches and floors should be grounded. The operator should be grounded using a wrist strap. Semiconductor devices must not be touched with bare hands. Similar precautions need to be taken for PW boards with mounted semiconductor devices.

(4) STATUS BEFORE INITIALIZATION: Power-on does not necessarily define the initial status of a MOS device. Immediately after the power source is turned ON, devices with reset functions have not yet been initialized. Hence, power-on does not guarantee output pin levels, I/O settings or contents of registers. A device is not initialized until the reset signal is received. A reset operation must be executed immediately after power-on for devices with reset functions.

(5) POWER ON/OFF SEQUENCE: In the case of a device that uses different power supplies for the internal operation and external interface, as a rule, switch on the external power supply after switching on the internal power supply. When switching the power supply off, as a rule, switch off the external power supply and then the internal power supply. Use of the reverse power on/off sequences may result in the application of an overvoltage to the internal elements of the device, causing malfunction and degradation of internal elements due to the passage of an abnormal current. The correct power on/off sequence must be judged separately for each device and according to related specifications governing the device.

(6) INPUT OF SIGNAL DURING POWER OFF STATE : Do not input signals or an I/O pull-up power supply while the device is not powered. The current injection that results from input of such a signal or I/O pull-up power supply may cause malfunction and the abnormal current that passes in the device at this time may cause degradation of internal elements. Input of signals during the power off state must be judged separately for each device and according to related specifications governing the device.